L Number	Hits	Search Text	DB	Time stamp
1	2	6274488.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:26
2	17	("4522845"   "4622735"   "4683645"   "4830971"   "4924294"   "4931353"   "5010032"   "5122479"   "5236865"   "5302538"   "5405806"   "5563100"   "5593923"   "5888888"   "6060392"   "6072222"   "6174774").PN.	USPAT	2004/03/12 13:16
3	167		USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:26
4	1188	gate same silicon same laser same amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:27
5	4	(explosive with \$2crystallization) and (gate same silicon same laser same amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:33
6	19	(explosive with \$2crystallization) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:52
7	421	(amorphous with silicon with gate) same (dop\$3 with amorphous) same (crystal or crystallization or crystalline or crystallized)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 16:34
8	41	((amorphous with silicon with gate) same (dop\$3 with amorphous) same (crystal or crystallization or crystalline or crystallized)) same laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:52
9	24	(((amorphous with silicon with gate) same (dop\$3 with amorphous) same (crystal or crystallization or crystalline or crystallized)) same laser) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 15:18
10	22	((((amorphous with silicon with gate) same (dop\$3 with amorphous) same (crystal or crystallization or crystalline or crystallized)) same laser) and 438/\$3.ccls.) and (@ad<20010829 or @rlad<20010829)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 14:52
11	4228	melting with temperature with (silicon ajd dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 14:00
12	201	melting with temperature with (silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 14:00
13	8	("5405806"   "5432129"   "5624867"   "5861340"   "5888888"   "5953615"   "5981372"   "6365446").PN.	USPAT	2004/03/12 14:12
14	10	("5405806"   "5432129"   "5624867"   "5888888"   "5953615"   "5981372"   "6197646"   "6207563"   "6274511"   "6281102").PN.	USPAT	2004/03/12 14:14
15	21	·	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 14:52
16	19	((explosive with \$2crystallization) and (amorphous same dop\$3 same (crystal or crystallization or crystalline or crystallized))) and (@ad<20010829 or @rlad<20010829)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 15:17

17	3	(explosive with \$2crystallization) same	USPAT;	2004/03/12
		gate	US-PGPUB;	15:04
			EPO; JPO;	
			DERWENT	
18	53	amorphous same gate same molten	USPAT;	2004/03/12
1 10		amorphous same gave same moreen	US-PGPUB;	15:18
1	1		EPO; JPO;	13.10
1.0			DERWENT	0004/00/00
19	18	(amorphous same gate same molten) and	USPAT;	2004/03/12
1		438/\$3.ccls.	US-PGPUB;	15:18
1	1		EPO; JPO;	
1			DERWENT	
20	1	(explosive with \$2crystallization) and	USPAT;	2004/03/12
		((amorphous with silicon with gate) same	US-PGPUB;	16:35
		(dop\$3 with amorphous) same (crystal or	EPO; JPO;	
	Į.	crystallization or crystalline or	DERWENT	
		crystallized))	2-2	İ
l _	213204	257/\$3.ccls. or 438/\$3.ccls.	USPAT;	2004/03/12
	213204	2377 43.0013. 01 4307 43.0013.	· ·	13:14
			EPO; JPO;	13:14
		(055/40 3 400/40 3 4	DERWENT	
-	6		USPAT;	2002/04/09
		insulat\$3 and radiat\$3 and (amorphous	EPO; JPO;	09:46
		near2 silicon) and crystall\$7 and	DERWENT	
		explosive		
-	1	(257/\$3.ccls. or 438/\$3.ccls.) and (xcr	USPAT;	2002/04/09
		or (explosive adj recrystallization)) and	EPO; JPO;	09:58
		irradiat\$3 and dopant and gate	DERWENT	' ' ' '
_	103	(257/\$3.ccls. or 438/\$3.ccls.) and	USPAT;	2002/04/09
	103	recrystallization and irradiat\$3 and	EPO; JPO;	09:59
				09.39
	0.5	dopant and gate	DERWENT	2002/04/00
_	85		USPAT;	2002/04/09
		recrystallization and irradiat\$3 and	EPO; JPO;	15:19
		dopant and gate) and (amorphous adj	DERWENT	1
		silicon)		]
-	3	mosfet same (laser or irradiate) same	USPAT;	2002/04/09
l		amorphous same (dopant or dope)	EPO; JPO;	16:11
			DERWENT	1
l _	111	(laser or irradiate) same (amorphous adj	USPAT;	2002/04/10
· I	111	silicon) same (dopant or dope)	EPO; JPO;	16:52
ł		STITEON, Same (dopane of dope)	DERWENT	10.02
1_	10	((laser or irradiate) same (amorphous adj	USPAT;	2002/04/09
	10	silicon) same (dopant or dope)) same	EPO; JPO;	16:14
				10.14
	0.41	(insulat\$4 adj layer)	DERWENT	2002/04/00
1 -	241	mosfet with laser	USPAT;	2002/04/09
			EPO; JPO;	17:50
			DERWENT	
-	2	(mosfet with laser) same (amorphous adj	USPAT;	2002/04/09
		silicon)	EPO; JPO;	17:52
			DERWENT	
-	12	(mosfet with laser) same (dope dopant	USPAT;	2002/04/09
		doped)	EPO; JPO;	18:06
			DERWENT	
_	42	(mosfet with laser) and ((dope dopant	USPAT;	2002/04/09
	""	doped) with gate)	EPO; JPO;	18:07
1		aopea, with gate,		10.07
	12553	/magfat on fat an man land?	DERWENT	2002/04/10
-	12557	(mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate	EPO; JPO;	17:18
1			DERWENT	, _ ,
_	158	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate) same (laser or irradiation)	EPO; JPO;	11:07
			DERWENT	
-	4	"5966605"	USPAT;	2002/04/10
			EPO; JPO;	11:07
			DERWENT	
_	54793	gate with silicon	USPAT;	2002/04/10
	0.,55	Jane 112011	EPO; JPO;	14:12
			DERWENT	
1_	6957	(/mosfot on fot on mos) same denée same		2002/04/10
1	693/	((mosfet or fet or mos) same dop\$3 same	USPAT;	
		gate) and (gate with silicon)	EPO; JPO;	14:12
1	1		DERWENT	

-	15744	gate near2 silicon	USPAT;	2002/04/10
			EPO; JPO;	14:12
			DERWENT	
_	2731	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate) and (gate near2 silicon)	EPO; JPO;	14:12
		gave, and (gave nears 2222000)	DERWENT	
_	234	(((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
	234	gate) and (gate near2 silicon)) and	EPO; JPO;	14:15
	]			14.15
	110	(laser or irradiate)	DERWENT	2000/04/10
-	110	((((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate) and (gate near2 silicon)) and	EPO; JPO;	16:15
		(laser or irradiate)) and amorphous and	DERWENT	
		(recrystallize or polycrystalline or		
		crystalline)		
-	13	"5937325"	USPAT;	2002/04/10
			EPO; JPO;	16:19
			DERWENT	
_	8	"6013928"	USPAT;	2002/04/10
			EPO; JPO;	16:20
			DERWENT	
_	34	(laser or irradiate) same (amorphous adj	USPAT;	2002/04/10
		silicon) same ((dopant or dope) and	EPO; JPO;	16:53
		(sputter or deposition or evaporation))	DERWENT	=
1_	3488	(mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
-	3400	gate same (sputter or evaporat\$3 or	EPO; JPO;	17:20
		deposit\$3)	DERWENT	11.20
	2050			2002/04/10
-	3958	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate) and (dop\$3 with (sputter or	EPO; JPO;	17:21
		deposit\$3 or evaporat\$3))	DERWENT	0000/04/10
-	137	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate) and (dop\$3 with (sputter or	EPO; JPO;	17:21
		evaporat\$3))	DERWENT	
-	41	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
· .		gate) same (dop\$3 with (sputter or	EPO; JPO;	17:25
		evaporat\$3))	DERWENT	!
-	75	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate) same (dop\$3 with (sputter\$3 or	EPO; JPO;	17:32
		evaporat\$3))	DERWENT	
-	320		USPAT;	2002/04/10
		with silicon) and (mos or fet or mosfet)	EPO; JPO;	17:46
		, , , , , , , , , , , , , , , , , , , ,	DERWENT	
_	35	(dop\$3 with (sputter\$3 or evaporat\$3)	USPAT;	2002/04/10
		with silicon) same (mos or fet or mosfet)	EPO; JPO;	17:35
		With Sirion, Same (mos or ros or morrow,	DERWENT	
_	28	(dop\$3 with (sputter\$3 or evaporat\$3)	USPAT;	2002/04/10
	20	with silicon) same laser	EPO; JPO;	17:51
		with bilitoon, bame label	DERWENT	- / • Ŭ -
1_	190	(dop\$3 with (sputter\$3 or evaporat\$3))	USPAT;	2002/04/10
1	190	(dop\$3 with (sputter\$3 or evaporat\$3))   same laser	EPO; JPO;	18:02
		Same Tabel	DERWENT	10.02
	2	"6165875"	USPAT;	2002/04/10
-	4	0103073		18:02
			EPO; JPO;	10.02
	0040		DERWENT	2002/04/11
-	2848	gate with (metal or cap or capped) with	USPAT;	2002/04/11
		(tungsten or tantalum or titanium or	EPO; JPO;	16:14
		platinum)	DERWENT	
-	331	(gate with (metal or cap or capped) with	USPAT;	2002/04/11
		(tungsten or tantalum or titanium or	EPO; JPO;	16:20
i	1	platinum) ) and laser	DERWENT	]
-	89	(gate with (metal or cap or capped) with	USPAT;	2002/04/11
	į	(tungsten or tantalum or titanium or	EPO; JPO;	16:20
		platinum) ) and laser and mosfet	DERWENT	
-	4	<sup>"</sup> 6077758"	USPAT;	2002/04/11
	1		JPO;	17:34
	•		DERWENT	
-	11867	(boron or indium or arsenic or	USPAT;	2002/04/15
	1	phosphorus) with (sputter\$3 or CVD or	EPO; JPO;	14:06
		evaporat\$3)	DERWENT	
_	12		USPAT;	2002/04/15
		phosphorus) with (sputter\$3 or CVD or	EPO; JPO;	14:02
		evaporat\$3)) same dopant same laser	DERWENT	
L	L	1 orapotatys,, same dopante same raser		

-	1098	((boron or indium or arsenic or	USPAT;	2002/04/15
		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:10
		or CVD or evaporat\$3)	DERWENT	
-	33	(((boron or indium or arsenic or	USPAT;	2002/04/15
		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	14:09
		or CVD or evaporat\$3)) same dopant	DERWENT	
_	239	((boron or indium or arsenic or	USPAT;	2002/04/15
	233	phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:13
	i			13.13
	1	or CVD or evaporat\$3) with surface	DERWENT	0000/04/15
-	46		USPAT;	2002/04/15
ł		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:14
		or CVD or evaporat\$3) with surface) and	DERWENT	
		laser		1
_	2	5966605.pn.	USPAT;	2002/09/13
			EPO; JPO;	13:14
			DERWENT	
l _	2	6365476.pn.	USPAT;	2002/09/13
	_	000017012111	EPO; JPO;	13:15
			DERWENT	13.13
	,	6274499 mm		2002/09/13
1 -	2	6274488.pn.	USPAT;	2002/09/13
			EPO; JPO;	13:16
	1		DERWENT	0000/05/55
-	2	6077758.pn.	USPAT;	2002/09/13
	Í		EPO; JPO;	13:16
	1		DERWENT	
-	1175	radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5	EPO; JPO;	12:17
		dopys and orystallizes	DERWENT	
l _	34	radiat\$3 same amorphous same silicon same	USPAT;	2002/12/08
-	34			12:12
		dop\$3 same crystalliz\$5	EPO; JPO;	12:12
			DERWENT	0000 (10 (00
-	12	(radiat\$3 same amorphous same silicon	USPAT;	2002/12/08
		same dop\$3 same crystalliz\$5) same gate	EPO; JPO;	12:12
			DERWENT	
-	350	radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:22
	1	dop\$3)	DERWENT	i
_	315	(radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:20
		dop\$3)) and laser	DERWENT	1
	181	((radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
_	101		EPO; JPO;	12:21
		dop\$3 and crystalliz\$5 and (gate with	1	12:21
		dop\$3)) and laser) and 438/\$3.ccls.	DERWENT	2002/12/00
-	181		USPAT;	2002/12/08
	1	dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:21
		dop\$3)) and laser) and 438/\$3.ccls.) and	DERWENT	
		@ad<20010829		
-	33	radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
1		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:59
		dop\$3 with amorphous)	DERWENT	
1 -	4		USPAT;	2002/12/08
1	1 '	dop\$3 with amorphous)	EPO; JPO;	13:04
		aspir aron amorphisms,	DERWENT	
I _	2	radiat\$3 same amorphous same	USPAT;	2002/12/08
1 -	2			13:08
1		(crystalliz\$5 with gate with dop\$3)	EPO; JPO;	13:00
1	1	1 11 142	DERWENT	2002 (12 (22
1 -	11	• • • • • • • • • • • • • • • • • • • •	USPAT;	2002/12/08
		same (gate with dop\$3)	EPO; JPO;	13:30
l			DERWENT	
-	28		USPAT;	2002/12/08
		(amorphous with gate with dop\$3)	EPO; JPO;	15:51
			DERWENT	
l -	3	("5872761"   "5994179"   "6054355").PN.	USPAT	2002/12/08
				14:00
_	11	gate with height with "500" with	USPAT;	2002/12/08
	**	(nanometer\$1 or nm)	EPO; JPO;	15:55
1		(omcccty1 of Imm)	DERWENT	1 -0.00
1_	62	gate with height with / 1400 " - 1200"	USPAT;	2002/12/08
1 -	62		1	1
1	ļ	"200" or "100") with (nanometer\$1 or nm)	EPO; JPO;	15:56
1			DERWENT	I

	<del></del>	C4.5.0.0.0	r <del></del>	
_	2	6159782.pn.	USPAT; EPO; JPO;	2003/06/03 14:19
-	144	xcr or (explosive adj \$2crystalliz\$4)	DERWENT USPAT;	2003/06/30
			US-PGPUB; EPO; JPO; DERWENT	15:59
-	0	(xcr or (explosive adj \$2crystalliz\$4)) and (laser same amorphous same	USPAT; US-PGPUB;	2003/06/30 15:57
		(polycrystalline or polysilicon))	EPO; JPO; DERWENT	2000
-	127	xcr and @ad<20010829	USPAT; US-PGPUB;	2003/06/30 16:00
_	0	(xcr and @ad<20010829) and laser and	EPO; JPO; DERWENT USPAT;	2003/06/30
		amorphous and (polycrystalline or polysilicon) and (dopant or boron)	US-PGPUB; EPO; JPO;	15:58
-	138	xcr	DERWENT USPAT; US-PGPUB;	2003/06/30 15:58
			EPO; JPO; DERWENT	13.30
-	0	(xcr and @ad<20010829) and 438/\$3.ccls.	USPAT; US-PGPUB;	2003/06/30 15:59
_	6	explosive adj \$2crystalliz\$4	EPO; JPO; DERWENT USPAT;	2003/06/30
		explosive adj vzciystalilizvi	US-PGPUB; EPO; JPO;	15:59
_	35	explosive adj \$2crystalliz\$5	DERWENT USPAT;	2003/06/30
			US-PGPUB; EPO; JPO; DERWENT	15:59
-	16	(explosive adj \$2crystalliz\$5) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO;	2003/06/30 16:42
-	15		DERWENT USPAT;	2003/06/30
	:	438/\$3.ccls.) and @ad<20010829	US-PGPUB; EPO; JPO; DERWENT	17:46
-	18	("4522845"   "4622735"   "4683645"   "4830971"   "4924294"   "4931353"   "5010032"   "5122479"   "5236865"   "5302538"   "5405806"   "5563100"   "5593923"   "5888888"   "6060392"   "6072222"   "6174774"   "6274488").PN.	USPAT	2003/06/30 16:02
-	10	· · · · · · · · · · · · · · · · · · ·	USPAT	2003/06/30 16:10
-	17	"4522845"   "4622735"   "4683645"   "4830971"   "4924294"   "4931353"   "5010032"   "5122479"   "5236865"   "5302538"   "5405806"   "5563100"   "5593923"   "5888888"   "6060392"   "6072222"   "6174774").PN.	USPAT	2003/06/30 16:23
-	646	l · · · · · · · · · · · · · · · · · · ·	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:40
-	277	(laser same gate same dop\$3 same silicon) same amorphous	USPAT; US-PGPUB; EPO; JPO;	2003/06/30 16:41
-	80	((laser same gate same dop\$3 same silicon) same amorphous) same temperature	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:41

-	74	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2003/06/30
		silicon) same amorphous) same	US-PGPUB;	17:51
		temperature) and @ad<20010829	EPO; JPO; DERWENT	
1_	41	((((laser same gate same dop\$3 same	USPAT;	2003/06/30
	]	silicon) same amorphous) same	US-PGPUB;	17:43
		temperature) and @ad<20010829) and	EPO; JPO;	17.45
		438/\$3.ccls.	DERWENT	
_	169	1 ' '	USPAT;	2003/06/30
		with silicon	US-PGPUB;	17:11
			EPO; JPO;	
	_		DERWENT	
-	7	(	USPAT	2003/06/30
		"5966605"   "5998272"   "6225176"		17:29
	3	"6297115").PN. laser same silicon same amorphous same	USPAT;	2003/06/30
-	3	wavelength same (pulse adj width) same	US-PGPUB;	17:45
		(irradiance or fluence) same (repetition	EPO; JPO;	17.45
		adj rate)	DERWENT	
<u>-</u>	19	1 -	USPAT;	2003/06/30
		width) same (irradiance or fluence) same	US-PGPUB;	17:50
		(repetition adj rate)	EPO; JPO;	
			DERWENT	
-	12		USPAT;	2003/06/30
İ		width) same (irradiance or fluence) same	US-PGPUB;	18:20
1		(repetition adj rate)) and @ad<20010829	EPO; JPO;	
	10	(/lagon game wavelength game /nulge add	DERWENT USPAT;	2003/06/30
-	10	((laser same wavelength same (pulse adj width) same (irradiance or fluence) same	USPAT; US-PGPUB;	17:46
	1	(repetition adj rate)) and @ad<20010829)	EPO; JPO;	17.30
	1	not ultratech	DERWENT	
_	293	laser and wavelength and (pulse adj	USPAT;	2003/06/30
		width) and (irradiance or fluence) and	US-PGPUB;	17:50
		(repetition adj rate)	EPO; JPO;	
			DERWENT	
-	0	1 , , , , = = 3	USPAT;	2003/06/30
		silicon) same amorphous) same	US-PGPUB;	17:51
		temperature) and @ad<20010829) and (laser and wavelength and (pulse adj width) and	EPO; JPO; DERWENT	
		(irradiance or fluence) and (repetition	DEKMENT	
		adj rate))	ĺ	
-	1	(laser same gate same dop\$3 same silicon)	USPAT;	2003/06/30
	_	and (laser and wavelength and (pulse adj	US-PGPUB;	17:52
	1	width) and (irradiance or fluence) and	EPO; JPO;	
		(repetition adj rate))	DERWENT	
-	1	(melting with temperature with amorphous	USPAT;	2003/06/30
	1	with silicon) and (laser and wavelength	US-PGPUB;	17:52
		and (pulse adj width) and (irradiance or fluence) and (repetition adj rate))	EPO; JPO; DERWENT	
_	7	(laser and wavelength and (pulse adj	USPAT;	2003/06/30
	· · · · · · · · · · · · · · · · · · ·	width) and (irradiance or fluence) and	US-PGPUB;	18:18
	1	(repetition adj rate)) and (dopant or	EPO; JPO;	
		impurity) and amorphous and silicon	DERWENT	
-	1416		USPAT;	2003/06/30
		silicon	US-PGPUB;	18:19
	1		EPO; JPO;	
1_	83	(diffus\$3 same amorphous same dop\$3 same	DERWENT USPAT;	2003/06/30
-	63	silicon) same laser	US-PGPUB;	18:19
	1	STITEOIL SAME TASET	EPO; JPO;	
			DERWENT	
-	1	(laser and wavelength and (pulse adj	USPAT;	2003/06/30
	_	width) and (irradiance or fluence) and	US-PGPUB;	18:20
	1	(repetition adj rate)) and ((diffus\$3	EPO; JPO;	
		same amorphous same dop\$3 same silicon)	DERWENT	
		same laser)	110000	2002/06/20
-	72		USPAT; US-PGPUB;	2003/06/30 18:21
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